CF<sub>4</sub>/Cl<sub>2</sub>/O<sub>2</sub> CF<sub>4</sub>/Cl<sub>2</sub> condition ①W film etching speed nm/min 54.5 94.9 © Silicon nitride oxide film etching speed nm/min 35.0 24.2 ③ resist film etching speed nm/min 61.7 94.2 @/@ 4.34 selectivity ratio 1.65 0)/(3) 1.01 0.89

Table 1

		3.4	(J)-3	(2)·2	22-1	ω2	œ.		No.	
Table 2	pressure: 1 Pa (constant)	500	500	500	500	500	500	(W)	ICP	condition
		20	20	20	20	20	20	(W)	Bias	
		CF4/Cl2/O2	CF4/Cl2/O2	CF4/Cl2/02	CF4/Cl2/O2	CF4/Cl2	CF4/CI2		gas	
	stant)	25/25/10	25/25/10	25/25/10	25/25/10	30/30	30/30	(sccm)	flow rate of gas etching time	
		120	100	80	60	120	60	(sec)	etching time	
		68.74	57.32	44.65	33.79	80.05	40.00	(nm)	AVERAGE	amount of reduction in GI film thickness
		82.4	73.0	58.6	42.7	97.7	50.8	(nm)	MAX	
		38.7	31.6	27.0	18.5	48.7	23.8	(nm)	NIN	
		43.7	41.4	31.6	24.2	49.0	27.0	(nm)	RANGE	ckness
	,									